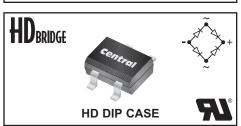


CBRHD SERIES

SURFACE MOUNT HIGH DENSITY 0.5 AMP **SILICON BRIDGE RECTIFIER**



- This series is UL listed: file number E130224
 Device is *Halogen Free* by design

FEATURES:

• Efficient use of board space: requires only 42mm² of board space vs. 120mm² of board space needed for industry standard 1.0 Amp surface mount bridge rectifier.



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHD series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING CODES:

CBRHD-02: CBD2 CBRHD-04: CBD4 CBRHD-06: CBD6 CBRHD-10: CBD10

- 50% higher density (Amps/mm²) than the industry standard 1.0 Amp surface mount bridge rectifier.
- · Glass passivated chips for high reliability.

		CBRHD	CBRHD	CBRHD	CBRHD	
MAXIMUM RATINGS : (T _A =25°C unless otherwise noted)	SYMBOL	- <u>02</u>	<u>-04</u>	<u>-06</u>	<u>-10 *</u>	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	1000	V
DC Blocking Voltage	v_R	200	400	600	1000	V
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	700	V
Average Forward Current (T _A =40°C) (Note 1)	lo		C).5		Α
Average Forward Current (T _A =40°C) (Note 2)	IO		C	0.8		Α
Peak Forward Surge Current	I _{FSM}		3	30		Α
Operating & Storage Junction Temperature	$T_{.I}, T_{sta}$		-65 t	o +150		°C

ELECTRICAL CHARACTERISTICS PER DIODE: (TA=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_{R}	V _R =Rated V _{RRM}		5.0	μΑ
I_{R}	V _R =Rated V _{RRM} , T _A =125°C		500	μΑ
V_{F}	I _F =400mA		1.0	V
$C_{.1}$	V _R =4.0V, f=1.0MHz	20		pF

Notes: (1) Mounted on Glass-Epoxy PCB.

(2) Mounted on Ceramic PCB.

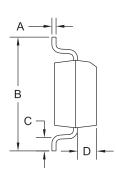
^{*} Available on special order, please consult factory.

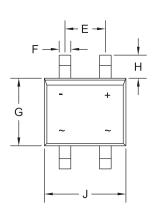
CBRHD SERIES

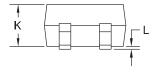
SURFACE MOUNT HIGH DENSITY 0.5 AMP SILICON BRIDGE RECTIFIER



HD DIP CASE - MECHANICAL OUTLINE







R2

MARKING CODES: CBRHD-02: CBD2 CBRHD-04: CBD4 CBRHD-06: CBD6 CBRHD-10: CBD10

DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
Α	0.006	0.014	0.15	0.35			
В	-	0.275	-	7.00			
С	0.027	0.043	0.70	1.10			
D	0.035	0.051	0.90	1.30			
E	0.090	0.106	2.30	2.70			
F	0.019	0.031	0.50	0.80			
G	0.150	0.165	3.80	4.20			
Н	0.051	0.067	1.30	1.70			
J	0.177	0.193	4.50	4.90			
K	0.090	0.106	2.30	2.70			
Ĺ	0.000	0.008	0.00	0.20			

HD DIP (REV: R2)

R4 (14-December 2011)